



SN0606G4

SiC Schottky Barrier Diode

Features

- Silicon Carbide Schottky Barrier Diode
- Low Vf
- Low IR
- High-Recovery Speed

Applications

- Switch mode power supplies
- Power Factor Correction
- Secondary Side Rectification
- PV Power Conditioners

Maximim Ratings (Ta=25°C)

| Parameter | Symbol | Conditions | Limit | Unit |
|-------------------------------------|--------|-----------------|-------------|------|
| Repetitive peak reverse voltage | VRM | | 650 | V |
| Reverse voltage (DC) | VR | | 650 | V |
| Forward current (DC) | lF | | 6 | Α |
| Surge no repetitive forward current | IFSM | 10ms Sinusoidal | 60 | Α |
| Junction temperature | Tj | | 175 | °C |
| Storage temperature | Tstg | | -55 to +175 | °C |

Electrical Characteristics (Ta=25°C)

| Parameter | Symbol | Condition | Min. | Тур. | Max. | Unit |
|-------------------------|--------|----------------------------|------|------|------|------|
| DC blocking voltage | VDC | Ir=30uA | 650 | - | - | V |
| Forward voltage | VF | I⊧=6A, Ta=25℃ | ı | 1.35 | 1.70 | V |
| | | I⊧=6A, Ta=150°C | ı | 1.63 | - | V |
| | | I⊧=6A, Ta=175°C | ı | 1.73 | - | V |
| Reverse current | lr | VR=650V, Ta=25℃ | - | 0.9 | 30 | uA |
| | | VR=650V, Ta=150°C | - | 6 | - | uA |
| | | VR=650V, Ta=175°C | ı | 10 | - | uA |
| Total capacitance | С | V _R =1V, f=1MHz | ı | 196 | - | pF |
| Total capacitive charge | Qc | VR=400V, di/dt=350A/us | - | 19 | - | nC |
| Switching time | tc | VR=400V, di/dt=350A/us | - | 15 | - | nS |

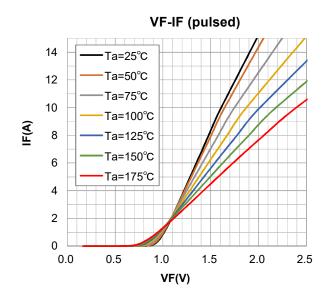


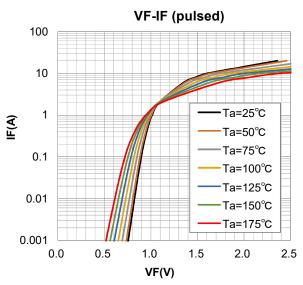


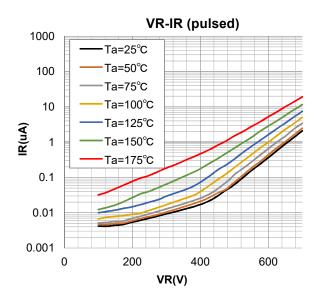
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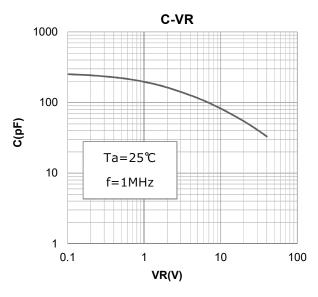
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Electrical Characteristics curves













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NOTE

- 1) This document is for reference only.
- 2) Please request for the specification sheet before use.
- 3) Since the products are in wafer form, the values in this document are for reference only.
- 4) Although we strive to improve the quality of our products, they may malfunction or fail. When using this product, please implement a safety design suitable for the system within your responsibility.
- 5) Although this document has been prepared with great care, we assume no responsibility for any damages incurred due to errors in the provoded information.
- 6) If the operating environment (e.g., high temperature, high voltage, high current) is severe, the reverse current may become excessively large and the device may be destroyed due to the increased reverse
- 7) The absolute maximum ratings must not be exceeded even momentarily. Do not exceed the absolute maximum ratings for any of the multiple ratings.
- 8) In particular, when evaluating or using the product in a resin-encapsulated package or in a sealed environment, be sure to measure the temperature and confirm that the maximum junction temperature designated as the maximum ratings is not exceeded.
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